# AIC HW3

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### Problem 1:

	Acm (V/V)	Adm (V/V)	CMRR (V/V)
(a)	165.6810m	-13.4153	79.7635
(b)	37.1281m	-4.0028	107.8105

### Problem 1 code:

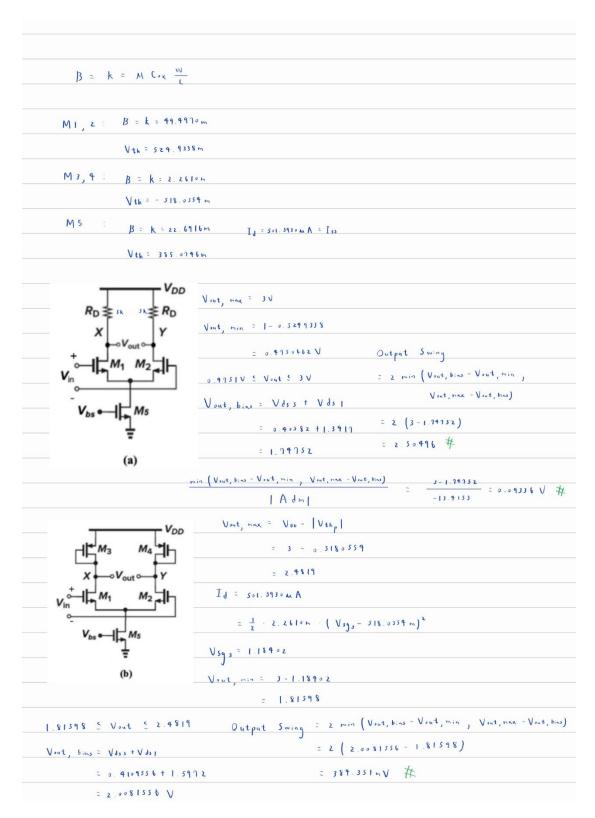
```
1. ***----***
2. *** setting
3. ***----***
4. .lib "~/U18_HSPICE_Model/mm180_reg18_v124.lib" tt
5. .TEMP 25
6. .op
7. ***----***
8. ***
       simulation
9. ***----***
10. .option post
11. .tran 0.1n 30u
12. .probe I(M1_n)
13. .probe I(M2_n)
14. .probe Vout=V(x,y)
15. *.DC Vgs 0V 1.8V 0.05V sweep T 0 80 10
17. ***----***
18. *** parameters
19. ***----***
20. .global VDD GND Vbs Vb
22. ***----***
23. ***
       measure
24. ***----***
```

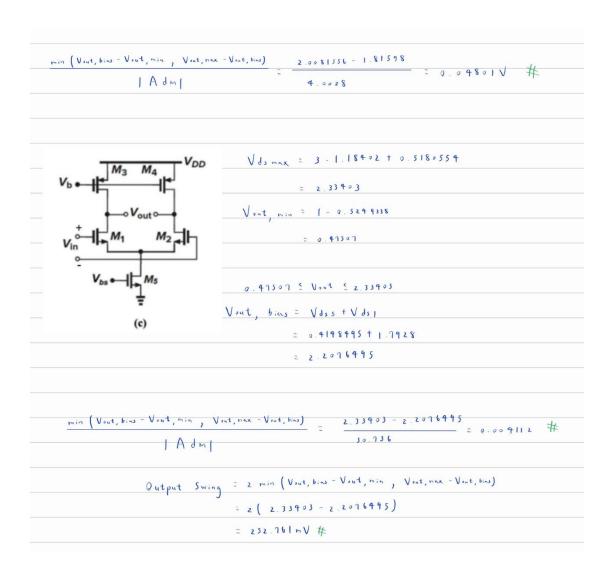
```
25. .meas tran Vx_max max v(x) from=0.1ns to=30us
26. .meas tran Vx_min min v(x) from=0.1ns to=30us
27. .meas tran Vx_Vpp param ='Vx_max - Vx_min'
29. .meas tran Vy_max max v(y) from=0.1ns to=30us
30. .meas tran Vy min min v(y) from=0.1ns to=30us
31. .meas tran Vy_Vpp param ='Vy_max - Vy_min'
32.
33. .meas tran Vin_max max v(V_diff+) from=0.1ns to=30us
34. .meas tran Vin_min min v(V_diff+) from=0.1ns to=30us
35. .meas tran Vin Vpp param = 'Vin max-Vin min'
36.
37. .meas tran Vout_max param ='Vx_max - Vy_min'
38. .meas tran Vout_min param ='Vx_min - Vy_min'
39. .meas tran Vout_Vpp param ='Vout_max - Vout_min'
41. .meas tran Vdiff_max max v(Vdiff) from=0.1ns to=30us
42. .meas tran Vdiff_min min v(Vdiff) from=0.1ns to=30us
43. .meas tran Vdiff_Vpp param ='Vdiff_max - Vdiff_min'
45. .meas tran Adm param ='-Vout_Vpp / Vdiff_Vpp'
46. *.meas tran Acm param ='-Vx_Vpp / Vin_Vpp'
47. *.meas tran CMRR param = 'Adm / Acm'
48.
49. *MAX tells Hspice to take the max value of V/I of variable during t1 \sim t2
50. ***----***
51. ***
          power/input
52. ***----***
53. Vsupply VDD GND 3v
54. *
                SIN(Offset Amplitude Freq. Delay)
55. V1
        Vbs GND 0.6v
56. V2
        Vb GND 2v
57. Vcm N0 GND 1v
58. V4
        Vdiff GND SIN(0 1m 100k 0)
59. EV+ V_diff+ N0 Vdiff GND +0.5
60. EV- V_diff- N0 Vdiff GND -0.5
61. ***-----***
62. *** circuit ***
```

```
63. ***-----***
64. R1 VDD X 5k
65. R2 VDD Y 5k
66. M1_n X V_diff+ Virtual
                                GND
                                       n_18_mm w=45u l=0.3u
67. M2_n Y V_diff- Virtual
                                 GND
                                       n_18_mm w=45u l=0.3u
68. M5 n Virtual Vbs
                          GND
                                 GND
                                       n 18 mm w=75u l=1u
69.
70. .subckt CKT_A Vin_pos Vin_neg X Y
71. R1 VDD X 5k
72. R2 VDD Y 5k
73. M1_n X Vin_pos V
                           GND
                                  n_18_mm w=45u l=0.3u
74. M2_n Y Vin_neg
                    V
                           GND
                                  n_18_mm w=45u l=0.3u
75. M5_n V Vbs
                                 n_18_mm w=75u l=1u
                   GND
                           GND
76. ends
77.
78. .subckt CKT_B Vin_pos Vin_neg X Y
79. M3_p X X
                    VDD
                           VDD
                                 p_18_mm w=10u l=0.3u
80. M4_p Y Y
                    VDD
                           VDD
                                 p_18_mm w=10u l=0.3u
81. M1_n X Vin_pos
                           GND
                                  n_18_mm w=45u l=0.3u
82. M2_n Y Vin_neg
                    V
                           GND
                                  n_18_mm w=45u l=0.3u
83. M5_n V Vbs
                   GND
                           GND
                                 n_18_mm w=75u l=1u
84. .ends
85.
86. .subckt CKT_C Vin_pos Vin_neg X Y
87. M3_p X Vb
                    VDD
                           VDD
                                  p_18_mm w=10u l=0.3u
88. M4_p Y Vb
                           VDD
                                 p_18_mm w=10u l=0.3u
                    VDD
89. M1_n X Vin_pos
                   V
                           GND
                                  n_18_mm w=45u l=0.3u
90. M2_n Y Vin_neg
                     V
                           GND
                                  n_18_mm w=45u l=0.3u
91. M5_n V Vbs
                   GND
                           GND
                                 n_18_mm w=75u l=1u
92. .ends
93.
94. .end
```

### Problem 2:

# **Derivation of Max Input Amplitude & Output Swing:**





	DC Gain	Vout, bias	Vout, min	Vout, max	Output	Max Input Signal
	(V/V)	(V)	(V)	(V)	Swing (V)	Amplitude (V)
(a)	-13.4151	1.748	0.475	3	2.505	93.36m
(b)	-4.0028	2.008	1.816	2.482	384.351m	48.01m
(c)	-30.7332	2.208	0.475	2.334	252.761m	4.112m

The circuits (a), (b), (c) are identical to 2.2 of handwrite handwork 2. We can use the same calculation methods employed in the handwrite homework to acquire the Vout, max & Vout, min.

The maximum output swing is defined as the difference between the maximum and minimum output voltages. This is limited by the bias voltage Vout, bias caused by setting Vicm to 1V. The output swing is given by the following equation:

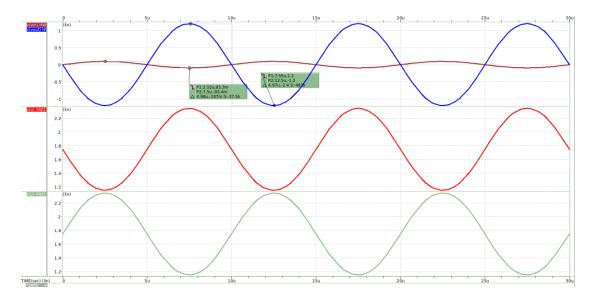
$$\textit{Output Swing} = 2 \text{min}(V_{\text{out,max}} \text{-} V_{\text{out,bias}}, V_{\text{out,bias}} \text{-} V_{\text{out,min}})$$

Next, to determine the max amplitude of the input signal, I use the following equation:

$$\frac{\min(V_{\text{out,max}} \cdot V_{\text{out,bias}}, V_{\text{out,bias}} \cdot V_{\text{out,min}})}{|A_{\text{dm}}|} = \textit{Max Input Amplitude}$$

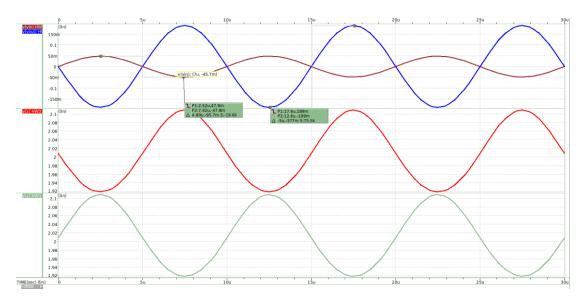
This helps us find a suitable input that satisfies the requirement of the problem and keeps all transistors in saturation.

### Circuit (a) Waveform & MOSFET Operating Region:



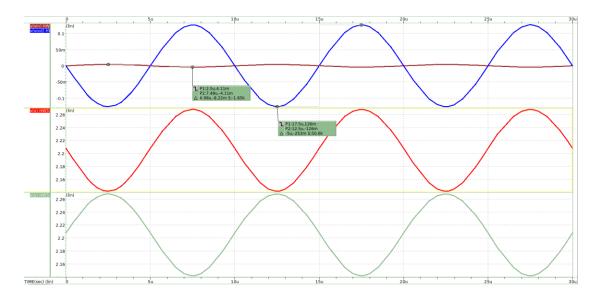
subckt			
element	0:m1_n	0:m2_n	0:m5_n
model	0:n_18_mm	0:n_18_mm	0:n_18_mm
region	Saturation	Saturation	Saturation
id	250.5004u	250.5004u	501.0008u
ibs	-1.3174f	-1.3174f	-7.450e-20
ibd	-5.6727f	-5.6727f	-2.1759f
vgs	594.1752m	594.1752m	600.0000m
vds	1.3417	1.3417	405.8248m
vbs	-405.8248m	-405.8248m	0.
vth	529.9849m	529.9849m	385.1133m
vdsat	114.5085m	114.5085m	200.5304m
vod	64.1902m	64.1902m	214.8867m
beta	49.4812m	49.4812m	22.6916m
gam eff	517.7531m	517.7531m	507.4463m
gm	3.8757m	3.8757m	4.0909m

### Circuit (b) Waveform & MOSFET Operating Region:



```
mosfets
subckt
                              0:m1 n
element
        0:m3_p
                   0:m4_p
                                        0:m2 n
                                                   0:m5 n
model
        0:p 18 mm 0:p 18 mm 0:n 18 mm
                                        0:n 18 mm
                                                   0:n 18 mm
region
        Saturation Saturation Saturation Saturation
 id
        -250.6965u -250.6965u 250.6965u 250.6965u 501.3930u
                                         -1.3341f -7.456e-20
 ibs
         2.453e-20 2.453e-20
                               -1.3341f
 ibd
         466.5857a 466.5857a
                               -6.5188f
                                        -6.5188f
                                                     -2.2034f
        -991.8423m -991.8423m 589.0444m 589.0444m 600.0000m
 vgs
 vds
        -991.8423m -991.8423m
                                 1.5972
                                           1.5972
                                                    410.9556m
                                                      0.
 vbs
           0.
                      0.
                              -410.9556m -410.9556m
 vth
        -518.0554m -518.0554m 524.9338m 524.9338m 385.0746m
 vdsat
        -444.3561m -444.3561m 114.4061m 114.4061m 200.5587m
        -473.7869m -473.7869m
 vod
                               64.1106m
                                          64.1106m 214.9254m
 beta
                      2.2610m
                               49.4970m
                                         49.4970m
                                                     22.6916m
           2.2610m
 gam eff
         557.0903m 557.0903m 517.8721m 517.8721m 507.4463m
         854.6328u 854.6328u
                                 3.8902m
                                           3.8902m
                                                      4.0941m
```

### Circuit (c) Waveform & MOSFET Operating Region:



```
subckt
element 0:m3_p
                  0:m4 p
                            0:m1 n
                                       0:m2 n
                                                 0:m5 n
model
        0:p_18_mm 0:p_18_mm
                            0:n_18_mm
                                       0:n_18_mm
                                                 0:n_18_mm
region
        Saturation Saturation Saturation Saturation
 id
        -250.8435u -250.8435u 250.8435u 250.8435u 501.6869u
 ibs
         2.455e-20 2.455e-20 -1.3467f -1.3467f -7.460e-20
         372.7140a 372.7140a -7.1666f -7.1666f
                                                  -2.2243f
 ibd
 vgs
          -1.0000
                   -1.0000
                             585.1505m 585.1505m 600.0000m
 vds
        -792.3054m -792.3054m
                               1.7928
                                         1.7928
                                                  414.8495m
                     0.
                            -414.8495m -414.8495m
                                                    0.
 vbs
           0.
        -518.0583m -518.0583m 521.0531m 521.0531m 385.0451m
 vth
        -450.7120m -450.7120m 114.3540m 114.3540m 200.5802m
 vdsat
 vod
        -481.9417m -481.9417m 64.0974m 64.0974m 214.9549m
 beta
           2.2567m
                     2.2567m 49.5082m 49.5082m
                                                   22.6916m
 gam eff 557.0903m 557.0903m 517.9622m 517.9622m 507.4463m
         834.7725u 834.7725u
                              3.9006m 3.9006m
                                                   4.0966m
```

### Code for Problem 2 & 3:

```
1. ***----**

2. *** setting ***

3. ***----***

4. .lib "~/U18_HSPICE_Model/mm180_reg18_v124.lib" tt

5. .TEMP 25

6. .op
```

```
7. ***----***
8. *** simulation
9. ***----***
10. .option post
11. .tran 0.1n 30u
12. .probe I(M1 n)
13. .probe I(M2_n)
14. .probe Vout=V(x,y)
15. *.DC Vgs 0V 1.8V 0.05V sweep T 0 80 10
17. ***----***
18. *** parameters
19. ***-----***
20. .global VDD GND Vbs Vb
21. ***-----***
22. *** power/input
23. ***-----***
24. Vsupply VDD GND 3v
25. *
             SIN(Offset Amplitude Freq. Delay)
26. V1 Vbs GND 0.6v
27. V2 Vb GND 2v
28. Vcm N0 GND 1v
29. V4 Vdiff GND SIN(0 1m 100k 0)
30. EV+ V_diff+ N0 Vdiff GND +0.5
31. EV- V_diff- N0 Vdiff GND -0.5
32. ***----***
33. ***
         circuit
34. ***-----***
35. R1 VDD X 5k
36. R2 VDD Y 5k
37. M1_n X V_diff+ Virtual GND n_18_mm w=45u l=0.3u
38. M2_n Y V_diff- Virtual
                          GND n_18_mm w=45u 1=0.3u
39. M5_n Virtual Vbs GND
                            GND
                                 n_18_mm w=75u l=1u
40.
41. .subckt CKT_A Vin_pos Vin_neg X Y
42. R1 VDD X 5k
43. R2 VDD Y 5k
44. M1_n X Vin_pos V GND n_18_mm w=45u l=0.3u
```

```
45. M2_n Y Vin_neg
                            GND
                                  n_18_mm w=45u l=0.3u
46. M5_n V Vbs
                     GND
                            GND
                                  n_18_mm w=75u l=1u
47. .ends
49. .subckt CKT_B Vin_pos Vin_neg X Y
50. M3 p X X
                                  p 18 mm w=10u l=0.3u
51. M4_p Y Y
                     VDD
                            VDD
                                  p_18_mm w=10u l=0.3u
52. M1_n X Vin_pos
                     V
                            GND
                                  n_18_mm w=45u l=0.3u
53. M2_n Y Vin_neg
                     V
                            GND
                                  n_18_mm w=45u l=0.3u
54. M5_n V Vbs
                   GND
                            GND
                                  n_18_mm w=75u l=1u
55. .ends
56.
57. .subckt CKT_C Vin_pos Vin_neg X Y
58. M3_p X Vb
                     VDD
                            VDD
                                  p_18_mm w=10u l=0.3u
59. M4_p Y Vb
                    VDD
                            VDD
                                  p_18_mm w=10u l=0.3u
60. M1_n X Vin_pos
                                  n_18_mm w=45u l=0.3u
                     V
                            GND
61. M2_n Y Vin_neg
                     V
                            GND
                                  n_18_mm w=45u l=0.3u
62. M5_n V Vbs
                GND
                            GND
                                  n_18_mm w=75u l=1u
63. .ends
64.
65. .end
```

#### **Problem 3:**

	DC Gain (V/V)	Rout ( $\Omega$ )	Output Swing(V)
(b)	-4.0028	2.0583k	1.33184
(c)	-30.7332	15.7615k	3.71792

(b) is a differential amplifier biased using diode-connected transistors M3 & M4, while (c) is biased using PMOS current sources. The diode-connected transistors provide a **fixed voltage drop** and are easier to implement, but they don't provide optimal performance in terms of output swing or gain. he diode connection reduces the voltage swing at the output because part of the supply voltage is consumed by the voltage drop across M3 and M4. The current-source biasing provides **higher output swing** and **better gain** compared to diode-connected

biasing. It also allows more flexibility in controlling the current flowing through the differential pair by adjusting Vb.

	Diode-Connected	Current Source
Pros	Simple to Implement	Higher Gain, Larger
		Output Swing
Cons	Sacrifices Gain, Output	More Complex to
	Swing & Input CM Range	Implement